Final datasheet
CoolSiC™ 1200 V SiC MOSFET G2 : Silicon Carbide MOSFET

Features

- V_{DSS} = 1200 V at T_{vj} = 25°C
- I_{DDC} = 102 A at T_C = 100°C
- $R_{DS(on)}$ = 12.2 mΩ at V_{GS} = 18 V, T_{vj} = 25°C
- Very low switching losses
- Overload operation up to T_{vj} = 200°C
- Short circuit withstand time 2 µs
- Benchmark gate threshold voltage, $V_{GS(th)}$ = 4.2 V
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- Suitable Infineon gate drivers can be found under https://www.infineon.com/gdfinder

Potential applications

- EV Charging
- Online UPS/Industrial UPS
- String inverter
- General purpose drives (GPD)
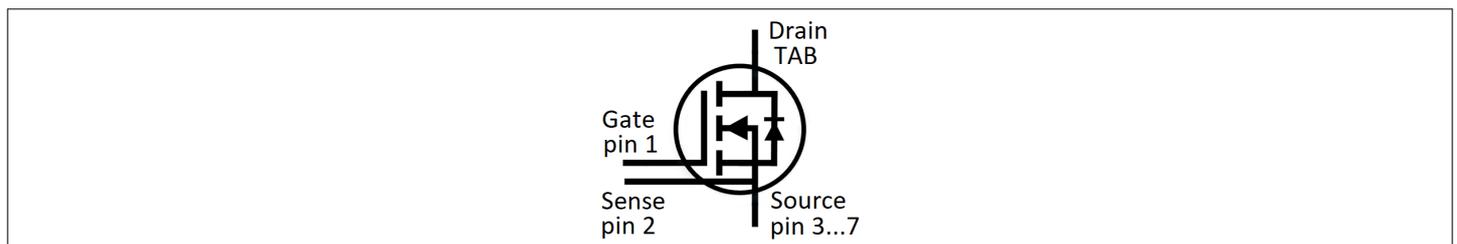
Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Description

Pin definition:

- Pin 1 - Gate
- Pin 2 - Kelvin sense contact
- Pin 3…7 - Source
- Tab - Drain

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction (only for 4pin, TO263-7L)

Halogen-free

Green

Lead-free

RoHS

Type	Package	Marking
IMBG120R012M2H	PG-TO263-7-U01	12M2H012

Table of contents

1 Package

Table 1 **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	reflow soldering (MSL1 according to JEDEC J-STD-020)			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.19	0.25	K/W

2 MOSFET

Table 2 **Maximum rated values**

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25$ °C		1200	V
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{DDC}	$V_{GS} = 18$ V	$T_C = 25$ °C	144	A
			$T_C = 100$ °C	102	
Peak drain current, t_p limited by $T_{vj(max)}$ [1]	I_{DM}	$V_{GS} = 18$ V		306	A
Gate-source voltage, max. transient voltage	V_{GS}	$t_p \leq 0.5$ µs, $D < 0.01$		-10...25	V
Gate-source voltage, max. static voltage [2]	V_{GS}			-7...23	V
Avalanche energy, single pulse	E_{AS}	$I_D = 56.7$ A, $V_{DD} = 50$ V, $L = 0.4$ mH		712	mJ
Avalanche energy, repetitive	E_{AR}	$I_D = 56.7$ A, $V_{DD} = 50$ V, $L = 2.2$ µH		3.56	mJ
Short-circuit withstand time	t_{SC}	$V_{DD} \leq 800$ V, $V_{DS,peak} < 1200$ V, $V_{GS(on)} = 15$ V, $T_{vj(start)} = 25$ °C		2	µs
Power dissipation, limited by $T_{vj(max)}$	P_{tot}		$T_C = 25$ °C	600	W
			$T_C = 100$ °C	300	

1) verified by design.
2) The maximum gate-source voltage in the application design should be in accordance to IPC-9592B.

Table 3 **Recommended values**

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-state resistance	$R_{DS(on)}$	I_D = 56.7 A	T_{vj} = 25 °C, $V_{GS(on)}$ = 18 V		12.2		mΩ
			T_{vj} = 150 °C, $V_{GS(on)}$ = 18 V		25	33	
			T_{vj} = 175 °C, $V_{GS(on)}$ = 18 V		28.9		
			T_{vj} = 25 °C, $V_{GS(on)}$ = 15 V		15.3		
Gate-source threshold voltage	$V_{GS(th)}$	I_D = 17.8 mA, V_{DS} = V_{GS} (tested after 1 ms pulse at V_{GS} = 20 V)	T_{vj} = 25 °C	3.5	4.2	5.1	V
			T_{vj} = 175 °C		3.2		
Zero gate-voltage drain current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = 0 V	T_{vj} = 25 °C			490	µA
			T_{vj} = 175 °C		8.4		
Gate leakage current	I_{GSS}	V_{DS} = 0 V	V_{GS} = 23 V			120	nA
			V_{GS} = -10 V			-120	
Forward transconductance	g_{fs}	I_D = 56.7 A, V_{DS} = 20 V			38.1		S
Internal gate resistance	$R_{G,int}$	f = 1 MHz, V_{AC} = 25 mV			4		Ω
Input capacitance	C_{iss}	V_{DD} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			4050		pF
Output capacitance	C_{oss}	V_{DD} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			176		pF
Reverse transfer capacitance	C_{rss}	V_{DD} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			15		pF
C_{oss} stored energy	E_{oss}	V_{DD} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			74		µJ
Output charge	Q_{oss}	Calculated by $C_{oss}(f)V_{DS}$ @100 kHz			275.3		nC
Effective output capacitance, energy related	$C_{o(er)}$	V_{DD} = 0...800 V, V_{GS} = 0 V			231.3		pF
Effective output capacitance, time related	$C_{o(tr)}$	I_D = constant, V_{DD} = 0...800 V, V_{GS} = 0 V			344.1		pF
Total gate charge	Q_G	V_{DD} = 800 V, I_D = 56.7 A, V_{GS} = -2/18 V, turn-on pulse			124		nC

(table continues...)

Table 4   (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Plateau gate charge	$Q_{GS(pl)}$	V_{DD} = 800 V, I_D = 56.7 A, V_{GS} = -2/18 V, turn-on pulse			26		nC
Gate-to-drain charge	Q_{GD}	V_{DD} = 800 V, I_D = 56.7 A, V_{GS} = -2/18 V, turn-on pulse			34		nC
Turn-on delay time	$t_{d(on)}$	V_{DD} = 800 V, I_D = 56.7 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		10		ns
			T_{vj} = 175 °C		10		
Rise time	t_r	V_{DD} = 800 V, I_D = 56.7 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		20.6		ns
			T_{vj} = 175 °C		20		
Turn-off delay time	$t_{d(off)}$	V_{DD} = 800 V, I_D = 56.7 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		19.7		ns
			T_{vj} = 175 °C		34.5		
Fall time	t_f	V_{DD} = 800 V, I_D = 56.7 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		13.2		ns
			T_{vj} = 175 °C		15.5		
Turn-on energy	E_{on}	V_{DD} = 800 V, I_D = 56.7 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		620		µJ
			T_{vj} = 175 °C		1160		
Turn-off energy	E_{off}	V_{DD} = 800 V, I_D = 56.7 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		270		µJ
			T_{vj} = 175 °C		350		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Min.	Typ.	Max.	Unit
Total switching energy[1]	E_{tot}	V_{DD} = 800 V, I_D = 56.7 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 2.3 Ω, $R_{GS(off)}$ = 2.3 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		970		µJ
			T_{vj} = 175 °C		1750		
Virtual junction temperature	T_{vj}			-55		175	°C
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h[2]				200	°C

1) including E_{fr}
2) up to 5000 cycles. Maximum ΔT limited to 100 K.

Note: The chip technology was characterized up to 200 kV/µs. The measured dV/dt was limited by measurement test setup and package.

Characteristics at T_{vj} = 25°C, unless otherwise specified.

3 Body diode (MOSFET)

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq$ 25 °C	1200	V
Peak reverse drain current, t_p limited by $T_{vj(max)}$	I_{SM}	V_{GS} = 0 V	145	A

Table 6 Characteristic values

Parameter	Symbol	Note or test condition		Min.	Typ.	Max.	Unit
Drain-source reverse voltage	V_{SD}	I_{SD} = 56.7 A, V_{GS} = 0 V	T_{vj} = 25 °C		4.2	5.5	V
			T_{vj} = 100 °C		4.11		
			T_{vj} = 175 °C		4.05		
MOSFET forward recovery charge	Q_{fr}	V_{DD} = 800 V, I_{SD} = 56.7 A, V_{GS} = 0 V, $-di_{SD}/dt$ = 1000 A/µs, Q_{fr} includes also Q_C	T_{vj} = 25 °C		0.55		µC
			T_{vj} = 175 °C		1.06		
MOSFET peak forward recovery current	I_{frm}	V_{DD} = 800 V, I_{SD} = 56.7 A, V_{GS} = 0 V, $-di_{SD}/dt$ = 1000 A/µs, Q_{fr} includes also Q_C	T_{vj} = 25 °C		10.1		A
			T_{vj} = 175 °C		15.9		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
MOSFET forward recovery energy	E_{fr}	V_{DD} = 800 V, I_{SD} = 56.7 A, V_{GS} = 0 V, $-di_{SD}/dt$ = 1000 A/µs, Q_{fr} includes also Q_C	T_{vj} = 25 °C		80		µJ
			T_{vj} = 175 °C		240		
Virtual junction temperature	T_{vj}			-55		175	°C
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h[1]				200	°C

1) up to 5000 cycles. Maximum ΔT limited to 100 K.

4 Characteristics diagrams

Reverse bias safe operating area (RBSOA)

$I_{DS} = f(V_{DS})$

$T_{vj} \leq 200\ °C$, $V_{GS} = 0/18\ V$, $T_c = 25\ °C$
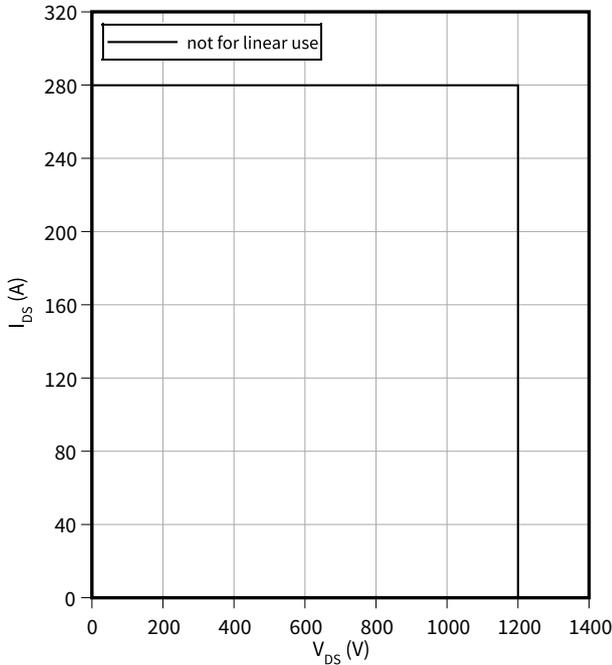
Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$
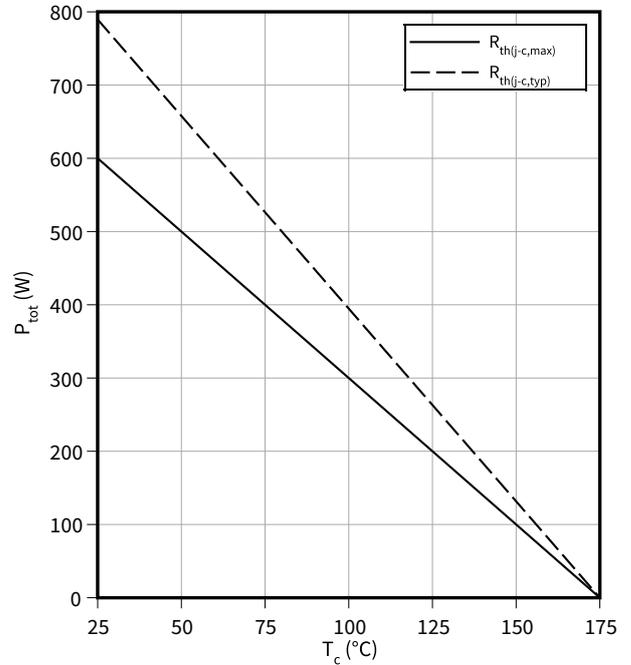
Maximum DC drain to source current as a function of case temperature limited by bond wire

$I_{DS} = f(T_c)$
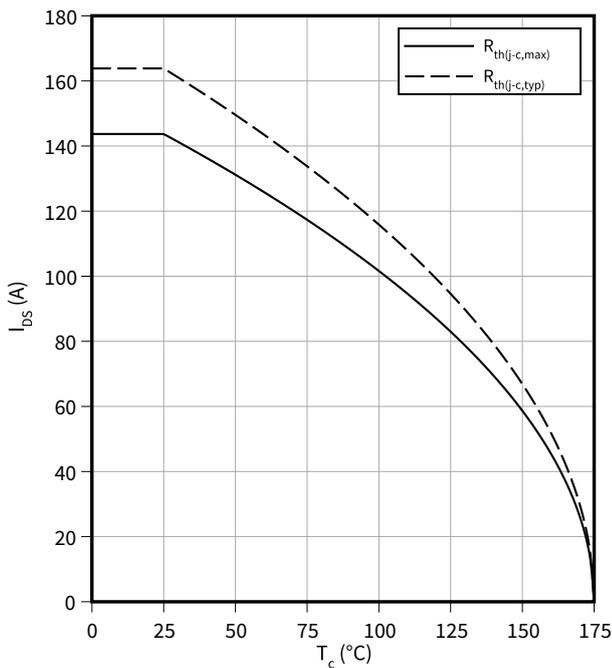
Maximum source to drain current as a function of case temperature limited by bond wire

$I_{SD} = f(T_c)$

$V_{GS} = 0\ V$

Typical transfer characteristic

$I_{DS} = f(V_{GS})$

V_{DS} = 20 V, t_p = 20 μs
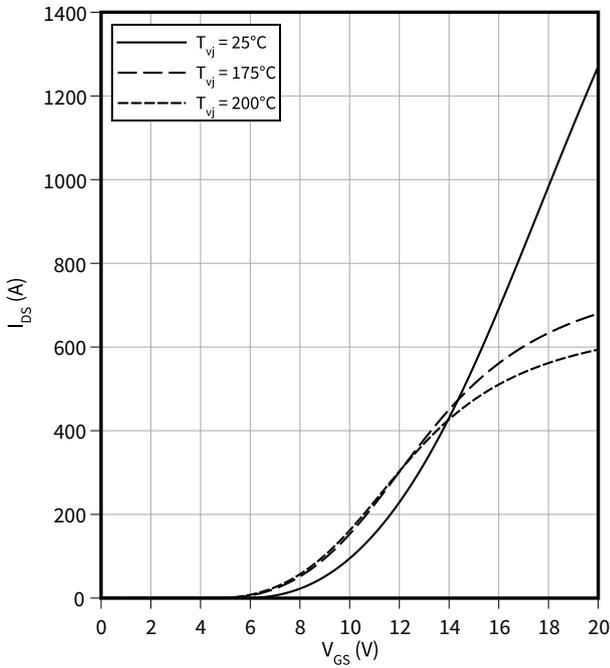
Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$

I_D = 17.8 mA
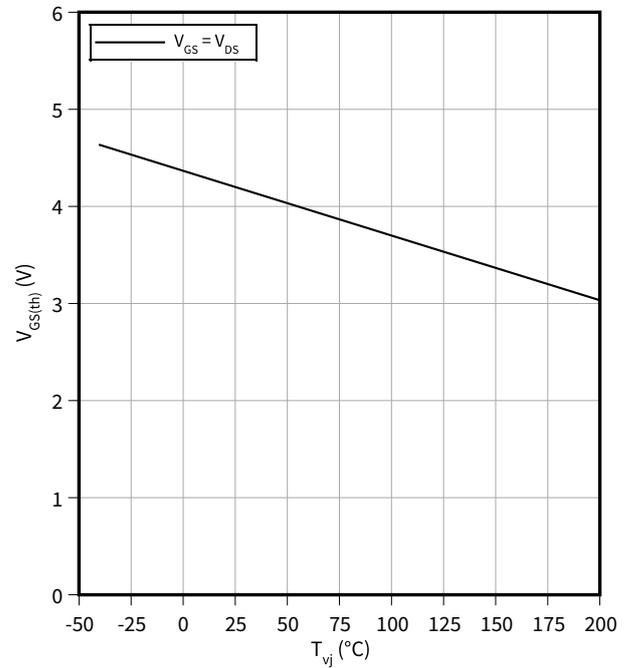
Typical output characteristic, V_{GS} as parameter

$I_{DS} = f(V_{DS})$

T_{vj} = 25 °C, t_p = 20 μs
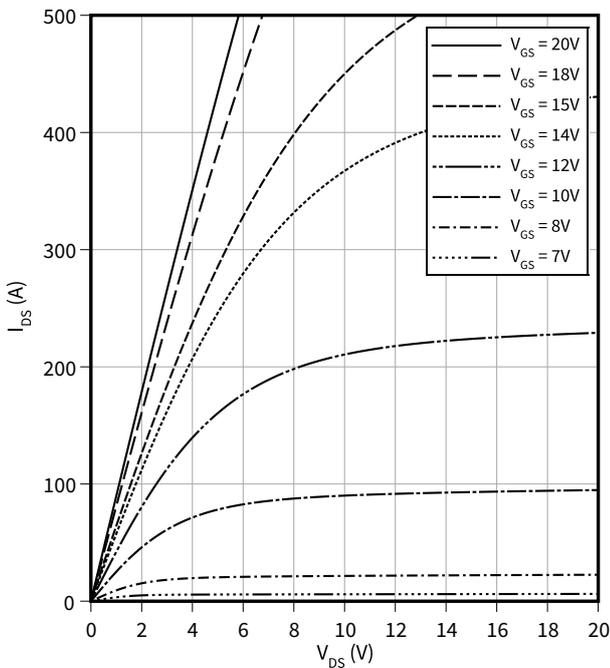
Typical output characteristic, V_{GS} as parameter

$I_{DS} = f(V_{DS})$

T_{vj} = 175 °C, t_p = 20 μs

Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$

$I_D = 56.7$ A
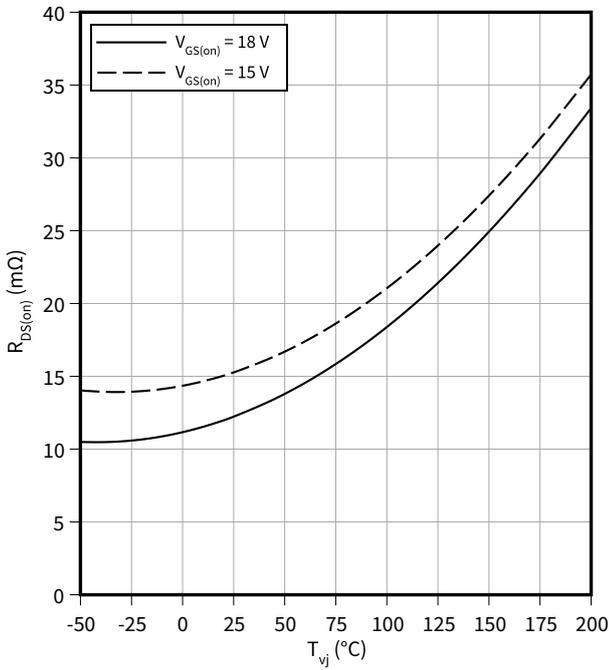
Typical gate charge

$V_{GS} = f(Q_G)$

$I_D = 56.7$ A, $V_{DS} = 800$ V
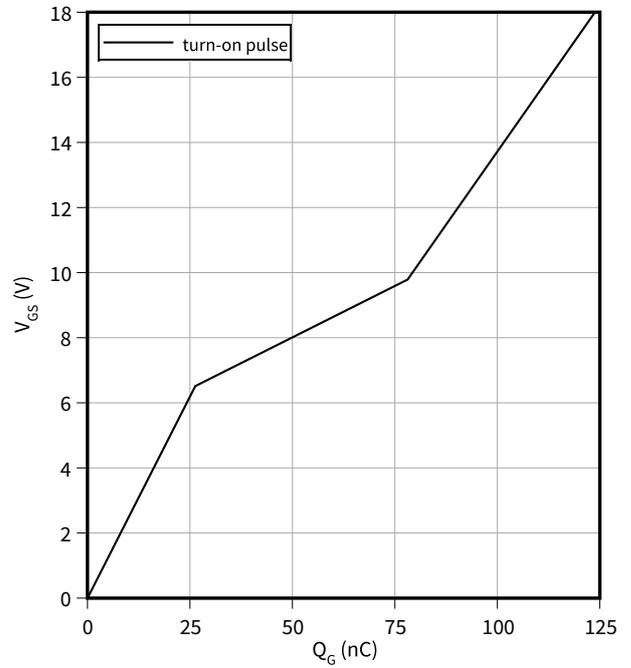
Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$

$f = 100$ kHz, $V_{GS} = 0$ V
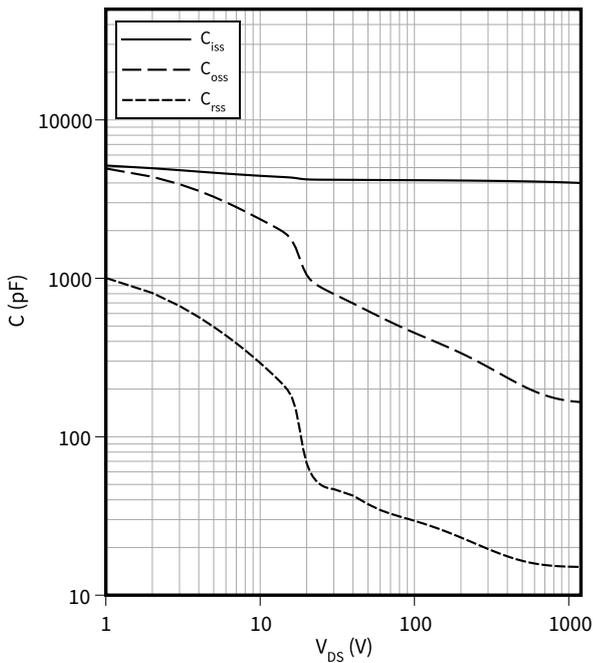
Typical reverse drain voltage as function of junction temperature

$V_{SD} = f(T_{vj})$

$I_{SD} = 56.7$ A, $V_{GS} = 0$ V

Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter

$I_{SD} = f(V_{SD})$

$T_{vj} = 25\ °C$, $t_p = 20\ μs$
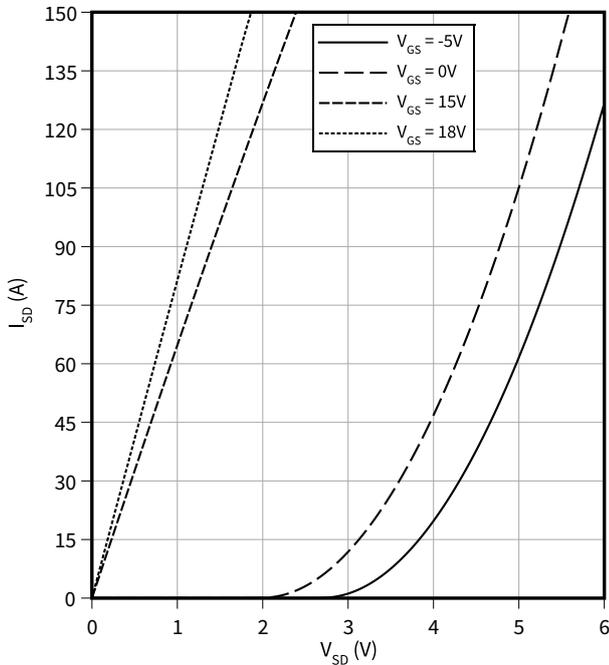
Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter
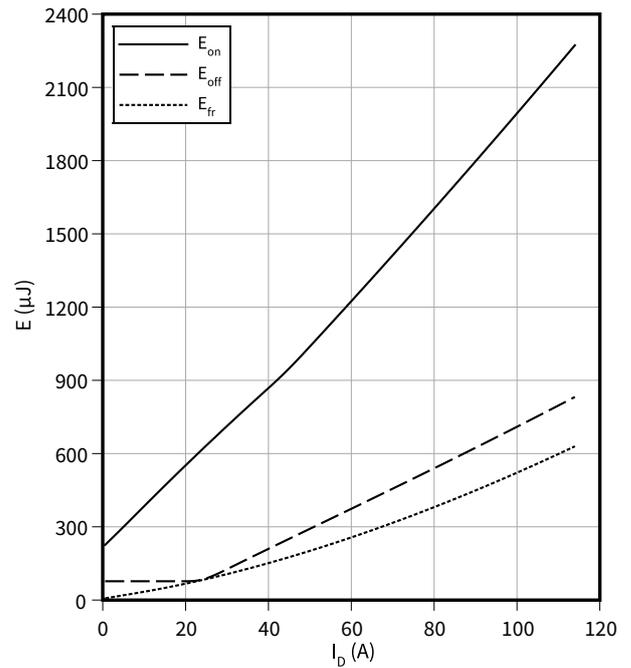
$I_{SD} = f(V_{SD})$

$T_{vj} = 175\ °C$, $t_p = 20\ μs$
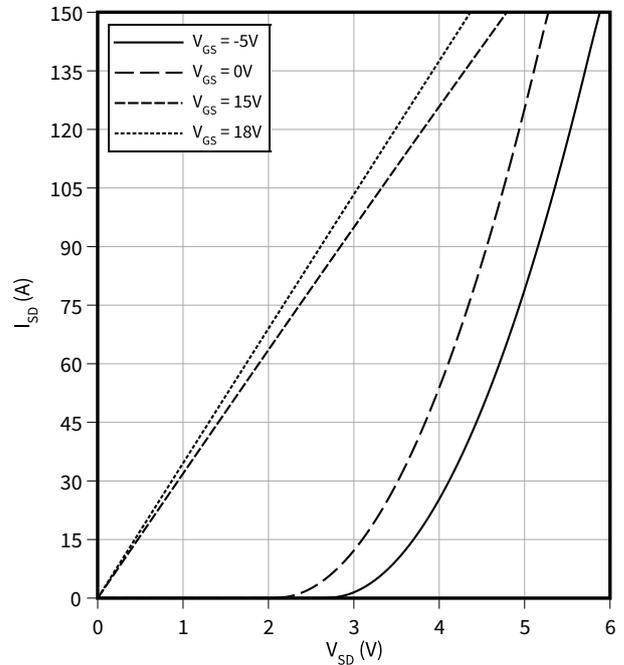
Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\ V$

$E = f(T_{vj})$

$V_{GS} = 0/18\ V$, $I_D = 56.7\ A$, $R_{G,ext} = 2.3\ Ω$, $V_{DD} = 800\ V$
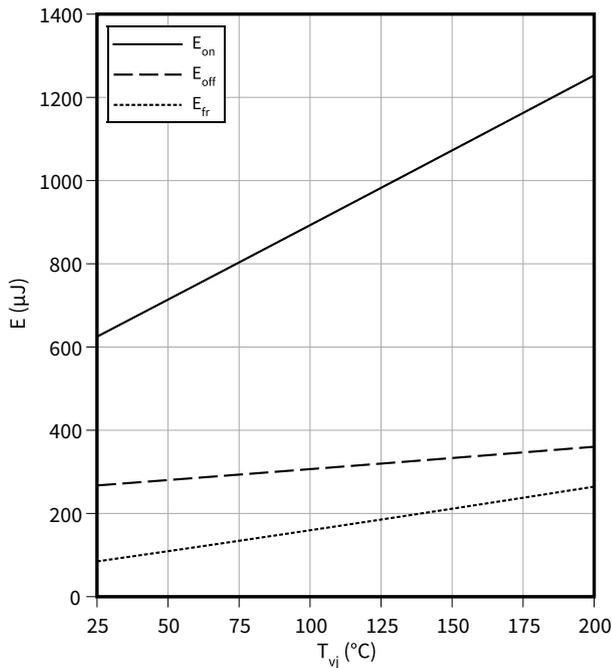
Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\ V$

$E = f(I_D)$
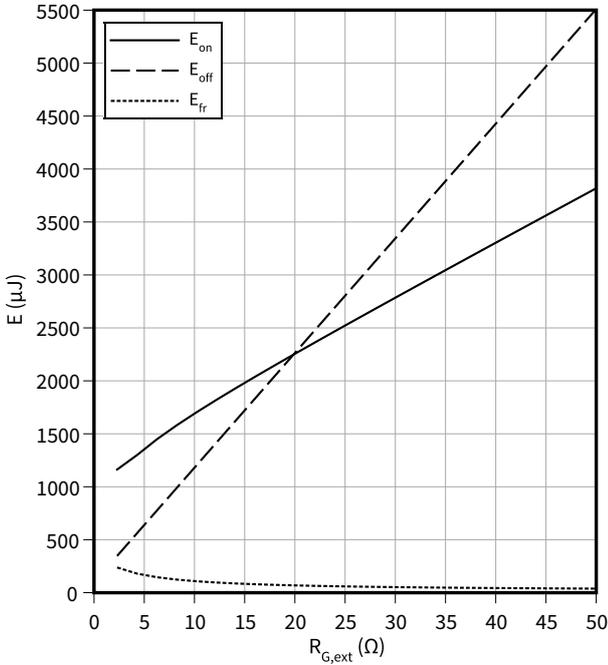
$V_{GS} = 0/18\ V$, $T_{vj} = 175\ °C$, $R_{G,ext} = 2.3\ Ω$, $V_{DD} = 800\ V$

Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$E = f(R_{G,ext})$

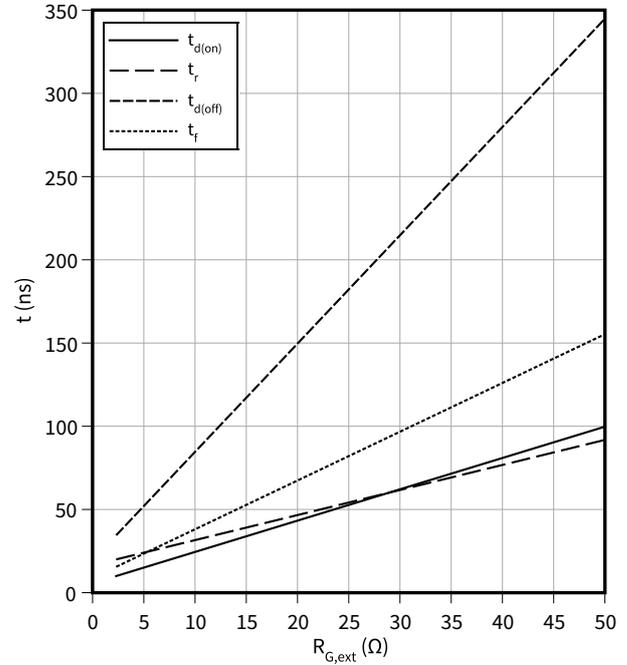V_{GS} = 0/18 V, I_D = 56.7 A, T_{vj} = 175 °C, V_{DD} = 800 V

Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$t = f(R_{G,ext})$

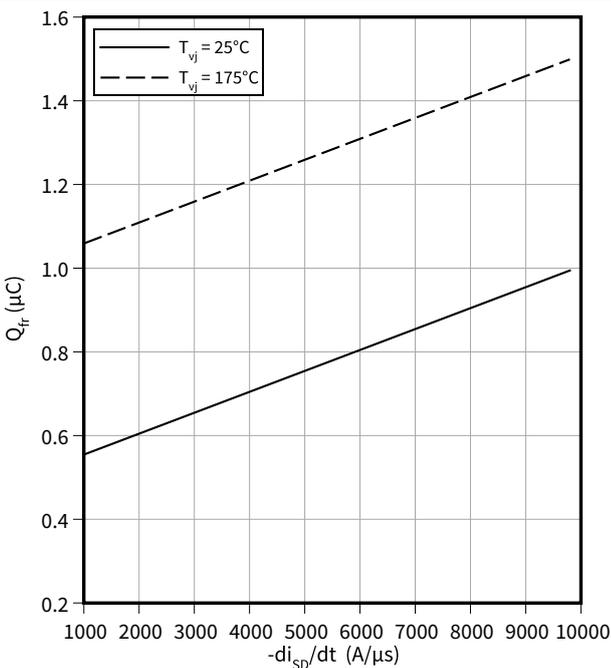V_{GS} = 0/18 V, I_D = 56.7 A, T_{vj} = 175 °C, V_{DD} = 800 V

Typical reverse recovery charge as a function of revere drain current slope, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V
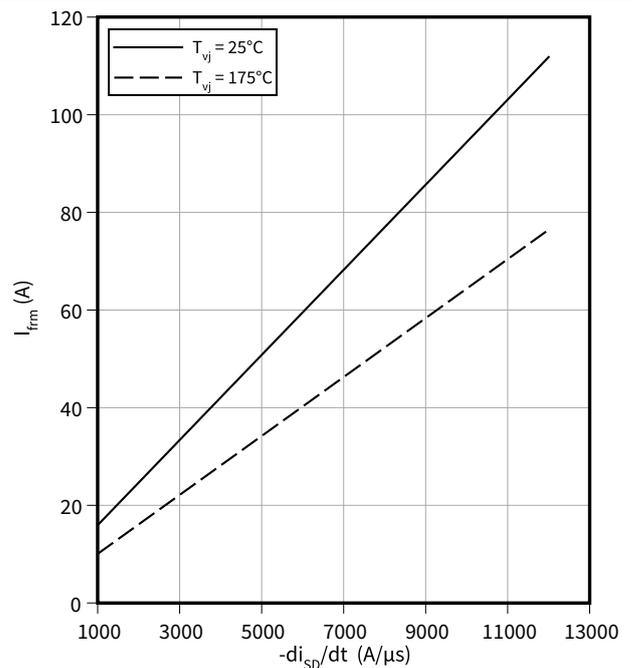
$Q_{fr} = f(-di_{SD}/dt)$

V_{GS} = 0/18 V, I_{SD} = 56.7 A, V_{DD} = 800 V

Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$I_{frm} = f(-di_{SD}/dt)$

V_{GS} = 0/18 V, I_{SD} = 56.7 A, V_{DD} = 800 V

Typical switching energy as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode: V_{GS} = -5 V

$E = f(t_{dead})$

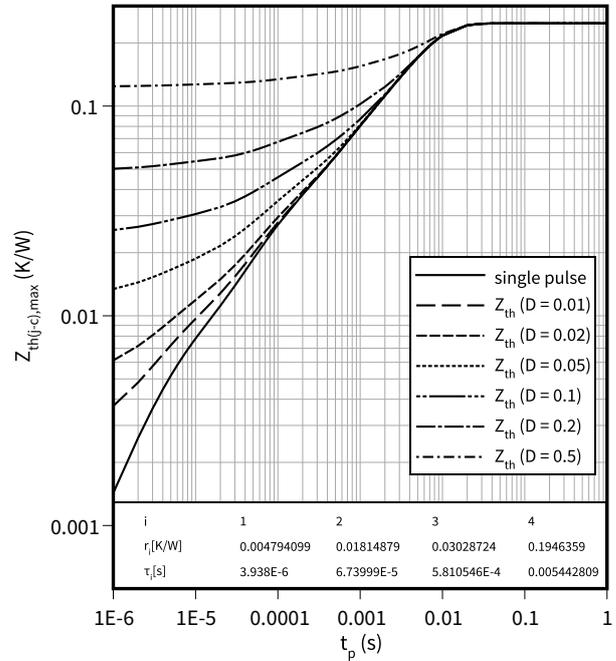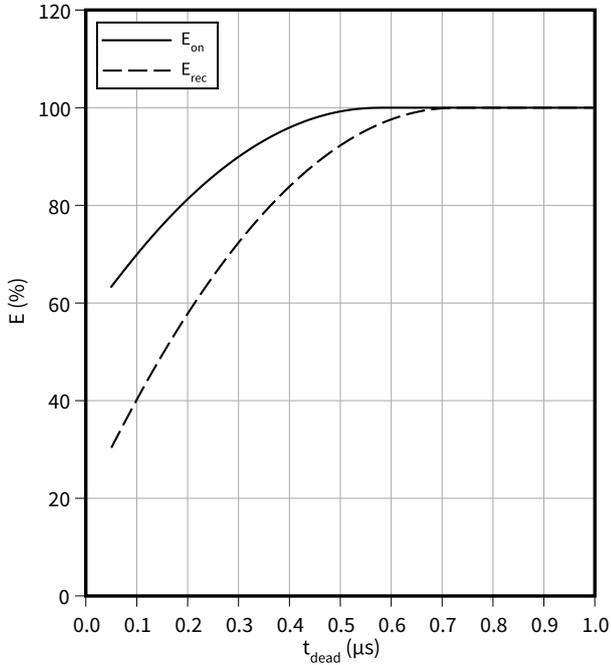V_{GS} = 0/18 V, I_D = 56.7 A, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω

V_{DD} = 800 V

Max. transient thermal impedance (MOSFET/diode)

$Z_{th(j-c),max} = f(t_p)$

$D = t_p/T$

i	1	2	3	4
r_i[K/W]	0.004794099	0.01814879	0.03028724	0.1946359
τ_i[s]	3.938E-6	6.73999E-5	5.810546E-4	0.005442809

5 Package outlines

PACKAGE - GROUP NUMBER:	**PG-TO263-7-U01**	
	MILLIMETERS	
DIMENSIONS	MIN.	MAX.
A	4.30	4.50
A1	0.00	0.10
A2	2.30	2.50
b	0.50	0.70
b1	0.00	0.15
c	0.40	0.60
c1	1.17	1.37
D	9.05	9.45
D1	5.90	6.10
E	9.80	10.20
E1	9.36	9.56
E2	0.00	0.30
E3	8.40	8.60
e	1.27	
H	15.00	
L	4.20	5.20
L1	0.70	1.30
L2	1.70	2.30
L3	2.70	
P	0.35	0.55
R	2.03	2.23
S	1.40	1.60
THETA	0.00°	8.00°

NOTES:

1) ALL METAL SURFACES TIN PLATED EXCEPT AREA OF CUT

2) MOLD FILLING IS ACCEPTABLE AT THIS AREA

Figure 1

6 Testing conditions

Figure A. **Definition of switching times**

Figure B. **Definition of body diode switching characteristics**

$$t_{fr} = t_a + t_b$$
$$Q_{fr} = Q_a + Q_b$$

Figure C. **Definition of switching losses**

$$E_{off} = {}_{t1}\int^{t2} V_{DS} * I_D * dt$$

$$E_{on} = {}_{t3}\int^{t4} V_{DS} * I_D * dt$$

Figure D. **Definition of QGD**

Figure E. **Thermal equivalent circuit**

Figure F. **Dynamic test circuit**
Parasitic inductance L_σ,
Parasitic capacitor C_σ,
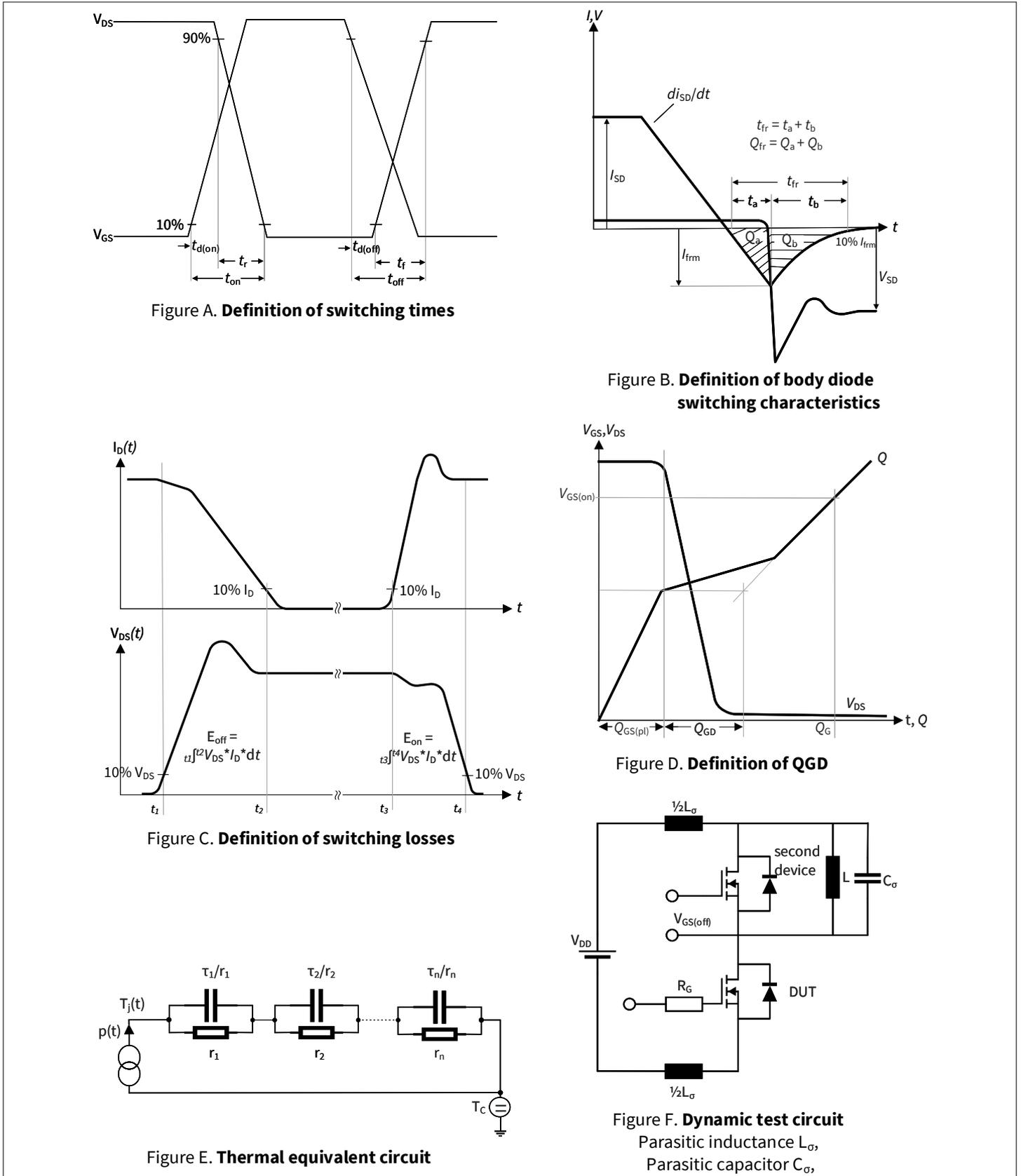
Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2023-08-08	Preliminary datasheet
1.00	2023-09-29	Final datasheet
1.10	2024-01-12	Negative gate voltage values updated
		Additional capacitance & charge values added
		$E = f(t_{dead})$ graph y-axis correction to percentage values
		Editorial changes
1.20	2024-06-26	Updated „Potential applications"
		Corrected package name
		Corrected static and dynamic gate-source voltage
		Corrected unit of L to µH for "Avalanche energy, repetitive"
		Corrected value of g_{fs} in the Table 4
		Corrected diagrams "Typical transfer characteristic" and "Max. transient thermal impedance (MOSFET/diode)"
		Updated Figure D. Definition of QGD

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SC015N065TCL SC013N120TCL SC021N120T8L SC032N120T8L YJD212080NCTG1 YJD212040NCFG2 SC015N065T8L

SC160N120T8L SC075N120T8L HC1M15120S SCT3080ALGC11 C3M0120100K C2M1000170J C3M0120090J C3M0065090J

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